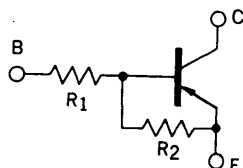


DESCRIPTION The BN1A4M is designed for use in medium speed switching circuit.

FEATURE • Bias resistors built-in type PNP transistor equivalent circuit.



$R_1 = 10 \text{ k}\Omega$

$R_2 = 10 \text{ k}\Omega$

ABSOLUTE MAXIMUM RATINGS

Maximum Temperatures

Storage Temperature -55 to $+150$ $^{\circ}\text{C}$

Junction Temperature 150 $^{\circ}\text{C}$ Maximum

Maximum Power Dissipation ($T_a = 25$ $^{\circ}\text{C}$)

Total Power Dissipation 250 mW

Maximum Voltages and Currents ($T_a = 25$ $^{\circ}\text{C}$)

V_{CBO} Collector to Base Voltage -60 V

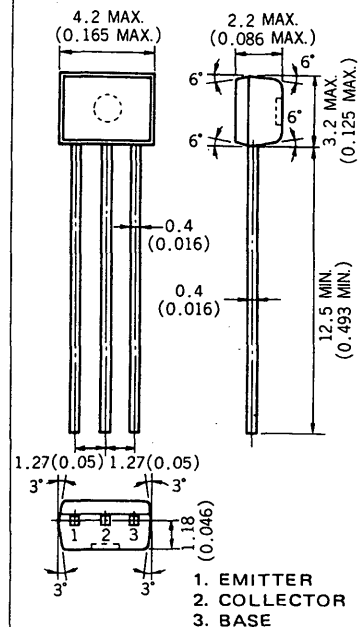
V_{CEO} Collector to Emitter Voltage -50 V

V_{EBO} Emitter to Base Voltage -10 V

$I_{C(DC)}$ Collector Current (DC) -100 mA

$I_{C(pulse)}$ Collector Current (pulse) -200 mA

PACKAGE DIMENSIONS in millimeters (inches)



ELECTRICAL CHARACTERISTICS ($T_a = 25$ $^{\circ}\text{C}$)

SYMBOL	CHARACTERISTIC	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
R_1	Input Resistance	7.0	10.0	13.0	$\text{k}\Omega$	
R_1/R_2	Resistors Ratio	0.9	1.0	1.1	—	
V_{IL}	Low Level Input Voltage		-1.13	-0.8	V	$V_{CE} = -5.0$ V, $I_C = -100$ μA
V_{IH}	Hi Level Input Voltage	-3.0	-1.6		V	$V_{CE} = -0.2$ V, $I_C = -5.0$ mA
t_{on}	Turn on Time		0.1	0.5	μs	$V_{CC} = -5.0$ V, $R_L = 1.0$ $\text{k}\Omega$ $V_{in} = -5.0$ V, $PW = 2$ μs , Duty Cycle ≤ 2 %
t_{stg}	Storage Time		0.95	3.0	μs	
t_{off}	Turn off Time		1.1	5.0	μs	
h_{FE1}	DC Current Gain	35	50	100	—	$V_{CE} = -5.0$ V, $I_C = -5.0$ mA
h_{FE2}	DC Current Gain	80	140		—	$V_{CE} = -5.0$ V, $I_C = -50$ mA
$V_{CE(sat)}$	Collector Saturation Voltage		-0.04	-0.2	V	$I_C = -5.0$ mA, $I_B = -0.25$ mA
I_{CBO}	Collector Cutoff Current			-0.1	μA	$V_{CB} = -50$ V, $I_E = 0$

TYPICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)